

ABSTRACT OF THE DISCLOSURE

In the solid-state image sensor comprising 4-Tr-pixels, TG lines connecting the gate electrodes 28_{TG} of the transfer transistors of the pixel units of the n^{th} row, and select lines connecting the gate electrodes 28_{SEL} of the select transistors of the pixel units of the $n+1^{th}$ row are formed of a common signal line, and the gate electrodes 28_{TG} of the pixels of the n^{th} row and the gate electrodes 28_{SEL} of the pixel units of the $n+1^{th}$ row are formed in one continuous pattern of the same conducting layer. Whereby allowance can be given to layouts of the metal interconnection layers. Accordingly, the floating diffusions FD can be effectively shielded from light. Furthermore, allowance can be given to the area. Accordingly, the floating diffusions FD can have the area increased, whereby the junction leakage can be reduced.